

Product Summary (Typ. @ $V_{GS} = -4.5V$, $T_A = +25^\circ C$)

V_{DS}	$R_{DS(on)}$	Q_g	Q_{gd}	I_D
-25V	33m Ω	4.8nC	1.0nC	-5.2A

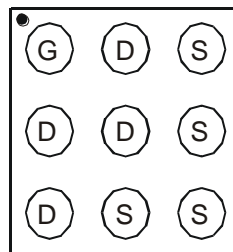
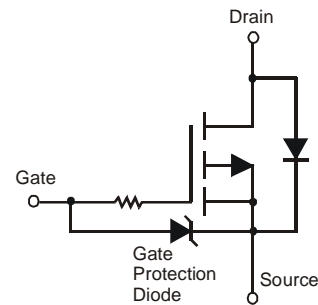
Features and Benefits

- LD-MOS Technology with the Lowest Figure of Merit:
 $R_{DS(on)} = 33m\Omega$ to Minimize On-State Losses
 $Q_g = 4.8nC$ for Ultra-Fast Switching
- $V_{gs(th)} = -0.6V$ typ. for a Low Turn-On Potential
- CSP with Footprint 1.5mm x 1.5mm
- Height = 0.62mm for Low Profile
- ESD = 6kV HBM Protection of Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**
- Qualified to AEC-Q101 Standards for High Reliability**

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Battery Management
- Load Switch
- Battery Protection


 Top-View
Pin Configuration


Equivalent Circuit

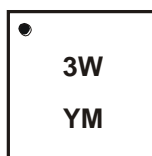
Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2540UCB9-7	U-WLB1515-9	3,000/Tape & Reel

- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 - See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information

U-WLB1515-9



3W = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: Y = 2011)
 M = Month (ex: 9 = September)

Date Code Key

Year	2011	2012	2013	2014	2015	2016	2017
Code	Y	Z	A	B	C	D	E

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	-25	V
Gate-Source Voltage			V _{GSS}	-6	V
Continuous Drain Current (Note 5) V _{GS} = -4.5V	Steady State	T _A = +25°C	I _D	-4.0	A
		T _A = +70°C		-3.0	
Continuous Drain Current (Note 6) V _{GS} = -4.5V	Steady State	T _A = +25°C	I _D	-5.2	A
		T _A = +70°C		-4.0	
Pulsed Drain Current (Pulse duration 10μs, duty cycle ≤1%)			I _{DM}	-30	A
Continuous Source Pin Current (Note 6)			I _S	-2.0	A
Pulsed Source Pin Current (Pulse duration 10μs, duty cycle ≤1%)			I _{SM}	-15	A
Continuous Gate Clamp Current (Note 5)			I _G	-0.6	A
Pulsed Gate Clamp Current (Pulse duration 10μs, duty cycle ≤1%)			I _{GM}	-8	A

Thermal Characteristics (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P _D	1.0	W
Total Power Dissipation (Note 6)	P _D	1.8	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	126.8	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	69	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-25	-	-	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current @T _C = +25°C	I _{DSS}	-	-	-1	μA	V _{DS} = -20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	-	-	-100	nA	V _{GS} = -6V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	-0.4	-0.6	-1.1	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	-	33	40	mΩ	V _{GS} = -4.5V, I _D = -2A
			42	50		V _{GS} = -2.5V, I _D = -2A
			52	60		V _{GS} = -1.8V, I _D = -2A
Forward Transfer Admittance	Y _{fs}	-	12	-	S	V _{DS} = -10V, I _D = -2A
Diode Forward Voltage (Note 5)	V _{SD}	-	-0.7	-1	V	V _{GS} = 0V, I _S = -2A
Reverse Recovery Charge	Q _{rr}	-	100	-	nC	V _{dd} = -9.5V, I _F = -2A, di/dt = 200A/μs
Reverse Recovery Time	t _{rr}	-	130	-	ns	
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iSS}	-	342	450	pF	V _{DS} = -10V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	-	174	225	pF	
Reverse Transfer Capacitance	C _{rSS}	-	70	90	pF	
Series Gate Resistance	R _G	-	28	35	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (4.5V)	Q _g	-	4.8	6.0	nC	V _{GS} = -4.5V, V _{DS} = -10V, I _D = -2A
Gate-Source Charge	Q _{gs}	-	0.5	-	nC	
Gate-Drain Charge	Q _{gd}	-	1.0	-	nC	
Turn-On Delay Time	t _{D(on)}	-	11	-	ns	V _{DD} = -10V, V _{GS} = -4.5V, I _{DS} = -2A, R _G = 2Ω,
Turn-On Rise Time	t _r	-	12	-	ns	
Turn-Off Delay Time	t _{D(off)}	-	56	-	ns	
Turn-Off Fall Time	t _f	-	42	-	ns	

- Notes:
- Device mounted on FR-4 PCB with minimum recommended pad layout.
 - Device mounted on FR4 material with 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to production testing.

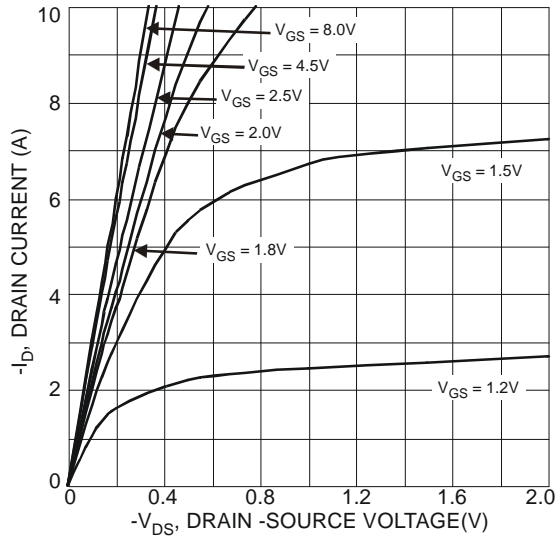


Fig. 1 Typical Output Characteristics

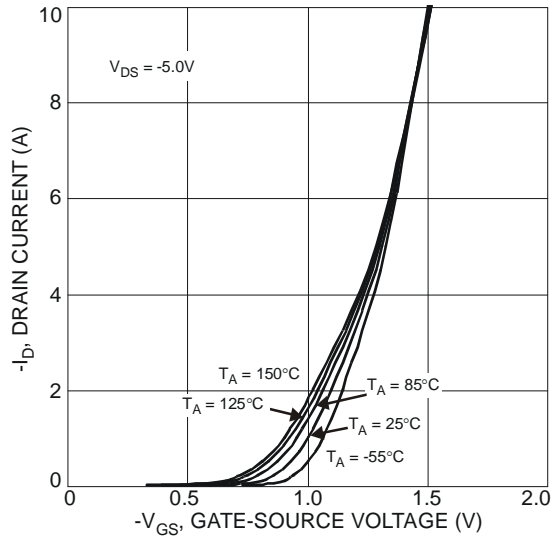


Fig. 2 Typical Transfer Characteristics

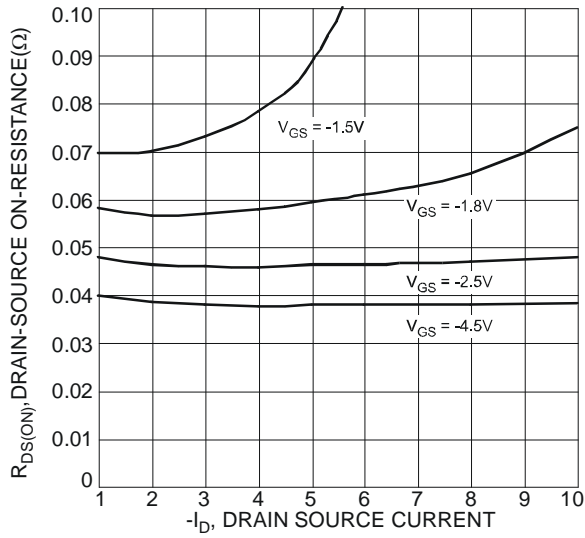


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

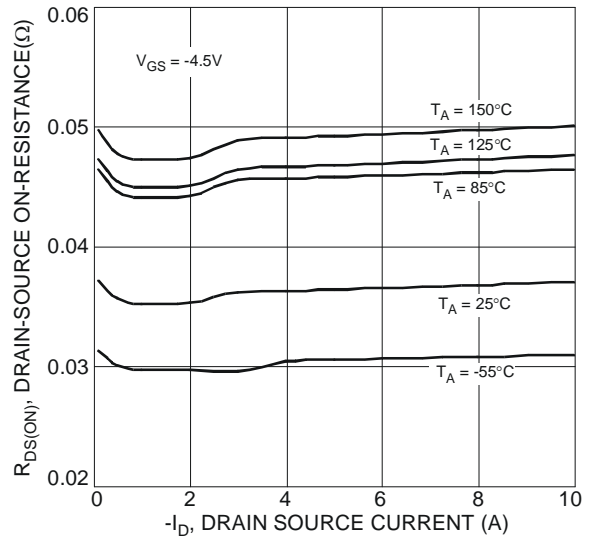


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

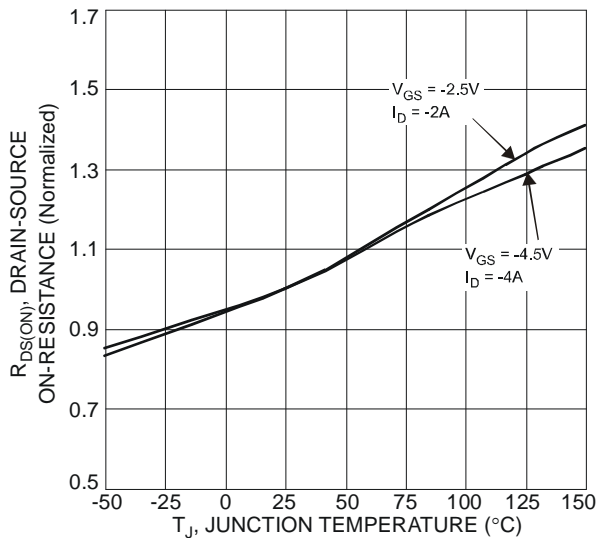


Fig. 5 On-Resistance Variation with Temperature

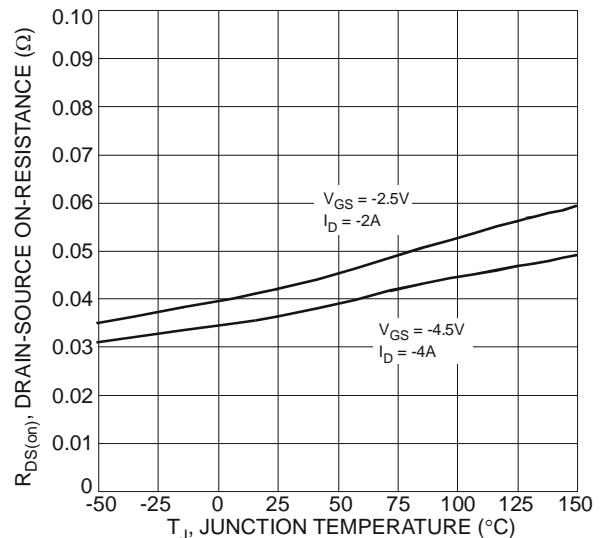


Fig. 6 On-Resistance Variation with Temperature

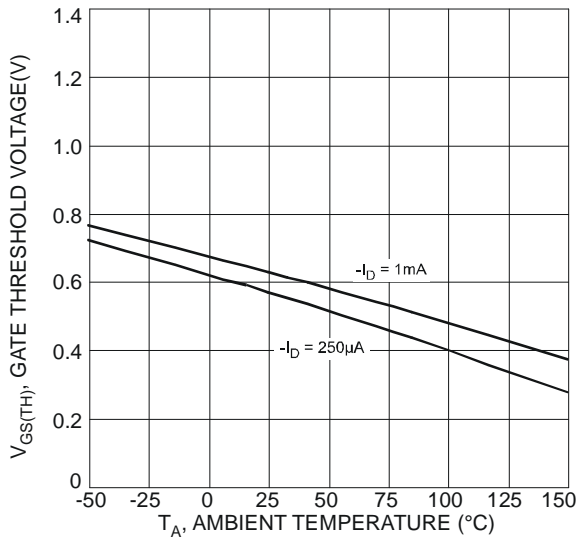


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

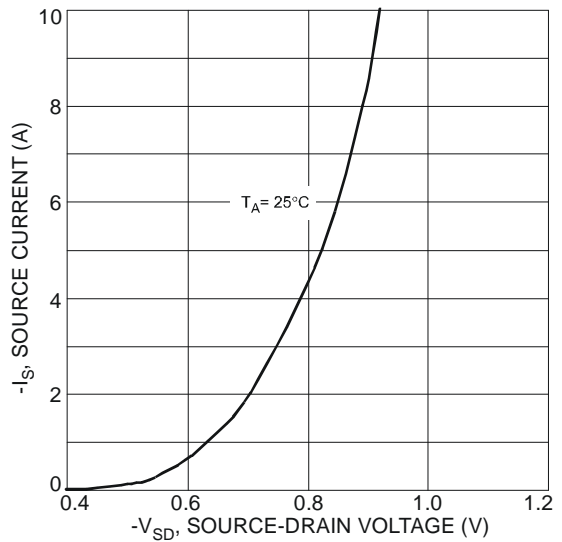


Fig. 8 Diode Forward Voltage vs. Current

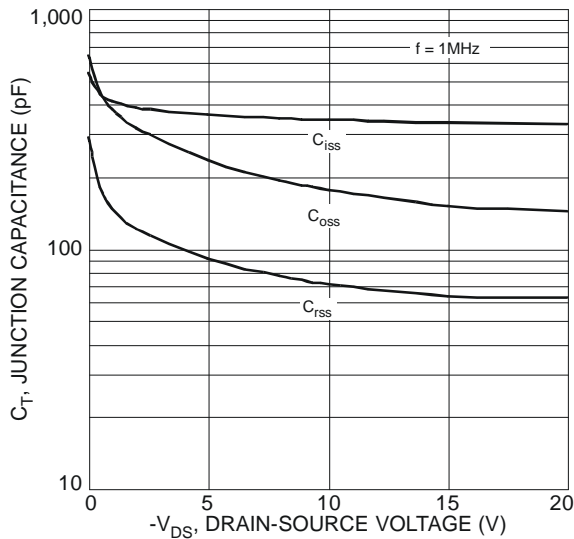


Fig. 9 Typical Junction Capacitance

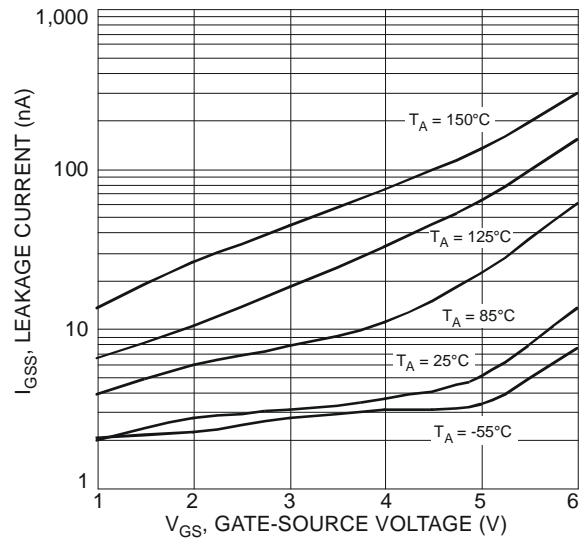


Fig. 10 Gate-Source Leakage Current vs. Voltage

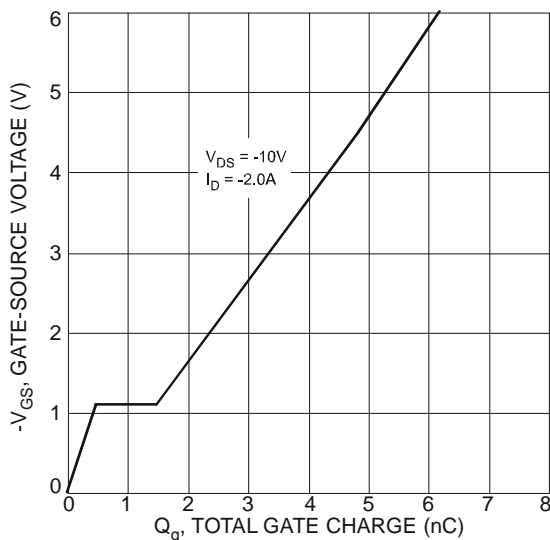


Fig. 11 Gate-Charge Characteristics

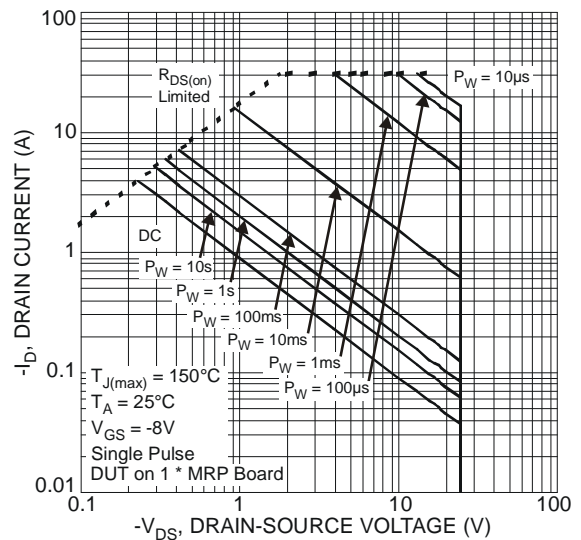
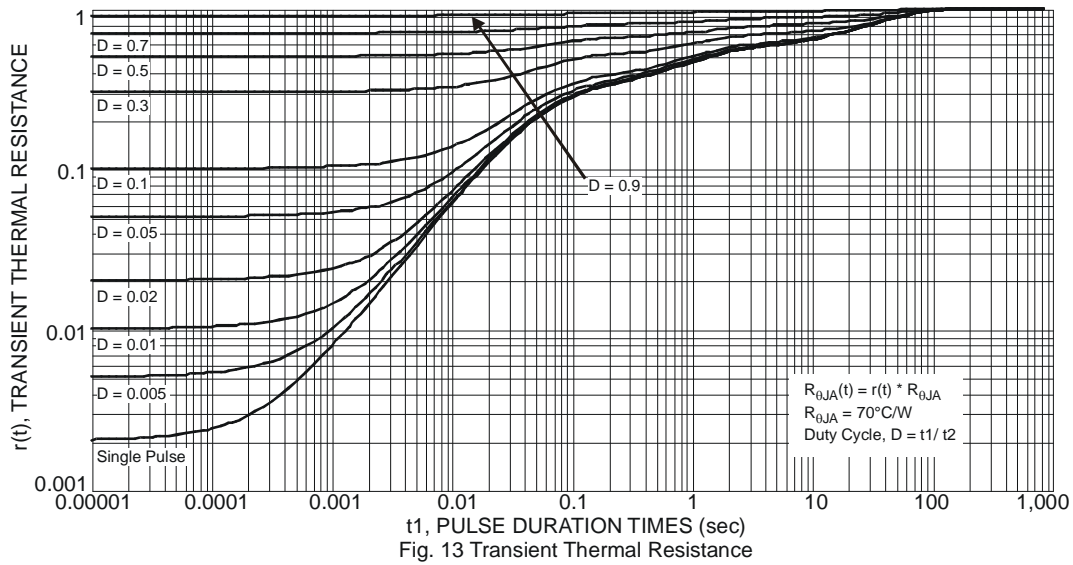
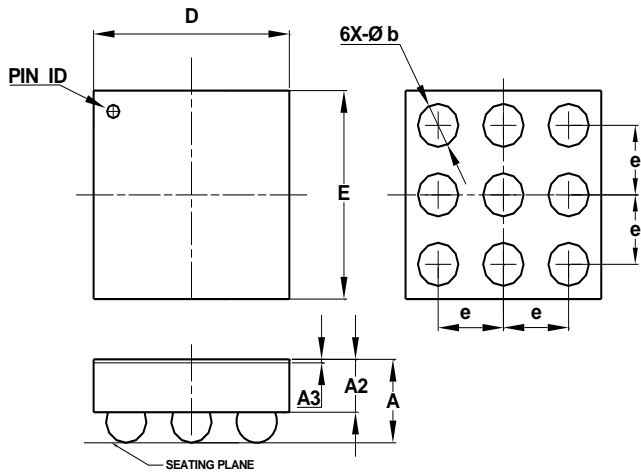


Fig. 12 SOA, Safe Operation Area



Package Outline Dimensions

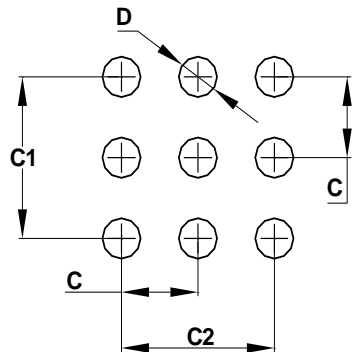
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



U-WLB1515-9			
Dim	Min	Max	Typ
A	-	0.62	-
A2	-	0.36	0.36
A3	0.020	0.030	0.025
b	0.27	0.37	0.32
D	1.47	1.51	1.49
E	1.47	1.51	1.49
e	-	-	0.50
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	0.50
C1	1.00
C2	1.00
D	0.25

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